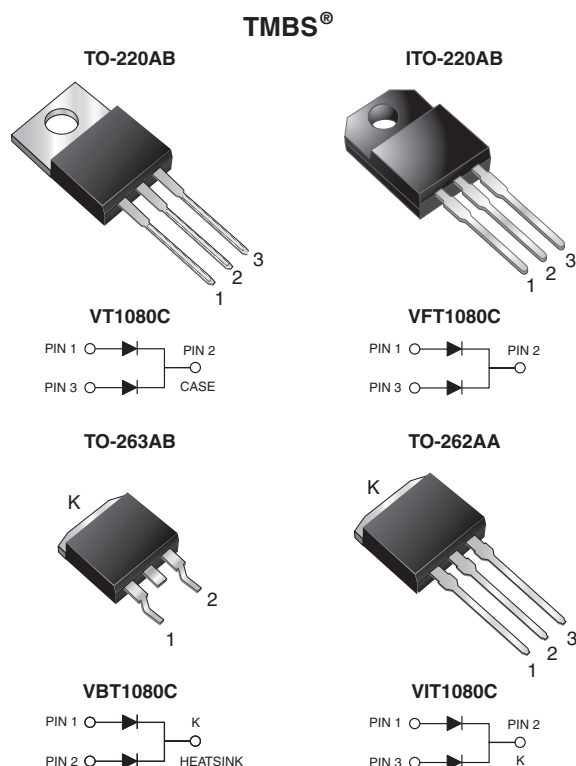


## Dual Trench MOS Barrier Schottky Rectifier

Ultra Low  $V_F = 0.49\text{ V}$  at  $I_F = 3\text{ A}$



### FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB, and TO-262AA package)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS  
COMPLIANT

### TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters and reverse battery protection.

### MECHANICAL DATA

**Case:** TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating  
Base P/N-E3 - RoHS-compliant, commercial grade

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

**Polarity:** as marked

**Mounting Torque:** 10 in-lbs maximum

### PRIMARY CHARACTERISTICS

|                             |                                            |
|-----------------------------|--------------------------------------------|
| $I_{F(AV)}$                 | 2 x 5 A                                    |
| $V_{RRM}$                   | 80 V                                       |
| $I_{FSM}$                   | 80 A                                       |
| $V_F$ at $I_F = 5\text{ A}$ | 0.57 V                                     |
| $T_J$ max.                  | 150 °C                                     |
| Package                     | TO-220AB, ITO-220AB,<br>TO-263AB, TO-262AA |
| Circuit configuration       | Common cathode                             |

### MAXIMUM RATINGS ( $T_A = 25\text{ °C}$ unless otherwise noted)

| PARAMETER                                                                                                |            | SYMBOL                            | VT1080C     | VFT1080C | VBT1080C | VIT1080C | UNIT |
|----------------------------------------------------------------------------------------------------------|------------|-----------------------------------|-------------|----------|----------|----------|------|
| Maximum repetitive peak reverse voltage                                                                  |            | V <sub>RRM</sub>                  | 80          |          |          |          | V    |
| Maximum average forward rectified current (fig. 1)                                                       | per device | I <sub>F(AV)</sub>                | 10          |          |          |          | A    |
|                                                                                                          | per diode  |                                   | 5           |          |          |          |      |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode             |            | I <sub>FSM</sub>                  | 80          |          |          |          | A    |
| Non-repetitive avalanche energy at T <sub>J</sub> = 25 °C, L = 60 mH per diode                           |            | E <sub>AS</sub>                   | 30          |          |          |          | mJ   |
| Peak repetitive reverse current at t <sub>p</sub> = 2 μs, 1 kHz, T <sub>J</sub> = 38 °C ± 2 °C per diode |            | I <sub>RRM</sub>                  | 1.0         |          |          |          | A    |
| Voltage rate of change (rated V <sub>R</sub> )                                                           |            | dV/dt                             | 10 000      |          |          |          | V/μs |
| Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min                                   |            | V <sub>AC</sub>                   | 1500        |          |          |          | V    |
| Operating junction and storage temperature range                                                         |            | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 |          |          |          | °C   |



| ELECTRICAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted) |                        |                         |                               |              |      |      |
|----------------------------------------------------------------------------|------------------------|-------------------------|-------------------------------|--------------|------|------|
| PARAMETER                                                                  | TEST CONDITIONS        |                         | SYMBOL                        | TYP.         | MAX. | UNIT |
| Breakdown voltage                                                          | I <sub>R</sub> = 10 mA | T <sub>A</sub> = 25 °C  | V <sub>BR</sub>               | 80 (minimum) | -    | V    |
| Instantaneous forward voltage per diode                                    | I <sub>F</sub> = 3 A   | T <sub>A</sub> = 25 °C  | V <sub>F</sub> <sup>(1)</sup> | 0.54         | -    | V    |
|                                                                            | I <sub>F</sub> = 5 A   |                         |                               | 0.63         | 0.72 |      |
|                                                                            | I <sub>F</sub> = 3 A   | T <sub>A</sub> = 125 °C |                               | 0.49         | -    |      |
|                                                                            | I <sub>F</sub> = 5 A   |                         |                               | 0.57         | 0.66 |      |
| Reverse current per diode                                                  | V <sub>R</sub> = 80 V  | T <sub>A</sub> = 25 °C  | I <sub>R</sub> <sup>(2)</sup> | 12           | 400  | μA   |
|                                                                            |                        | T <sub>A</sub> = 125 °C |                               | 6            | 15   | mA   |

**Notes**

(1) Pulse test: 300  $\mu\text{s}$  pulse width, 1 % duty cycle

(2) Pulse test: Pulse width  $\leq 40\text{ ms}$

| THERMAL CHARACTERISTICS ( $T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted) |            |                 |         |          |          |          |                      |
|--------------------------------------------------------------------------------------|------------|-----------------|---------|----------|----------|----------|----------------------|
| PARAMETER                                                                            |            | SYMBOL          | VT1080C | VFT1080C | VBT1080C | VIT1080C | UNIT                 |
| Typical thermal resistance                                                           | per diode  | $R_{\theta JC}$ | 3.5     | 6.5      | 3.5      | 3.5      | $^{\circ}\text{C/W}$ |
|                                                                                      | per device |                 | 2.5     | 5.5      | 2.5      | 2.5      |                      |

| ORDERING INFORMATION (Example) |                |                 |              |               |               |
|--------------------------------|----------------|-----------------|--------------|---------------|---------------|
| PACKAGE                        | PREFERRED P/N  | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |
| TO-220AB                       | VT1080C-E3/4W  | 1.88            | 4W           | 50/tube       | Tube          |
| ITO-220AB                      | VFT1080C-E3/4W | 1.70            | 4W           | 50/tube       | Tube          |
| TO-263AB                       | VBT1080C-E3/4W | 1.35            | 4W           | 50/tube       | Tube          |
| TO-263AB                       | VBT1080C-E3/8W | 1.35            | 8W           | 800/reel      | Tape and reel |
| TO-262AA                       | VIT1080C-E3/4W | 1.43            | 4W           | 50/tube       | Tube          |



## RATINGS AND CHARACTERISTICS CURVES ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

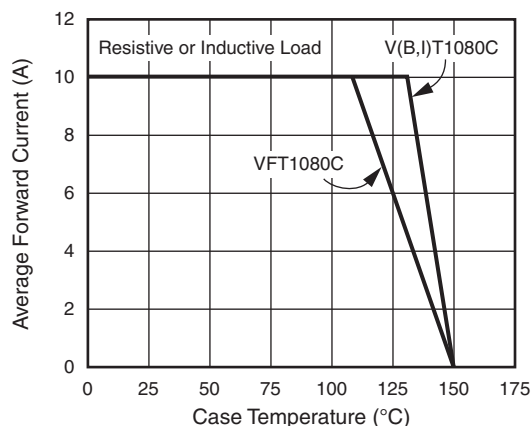


Fig. 1 - Maximum Forward Current Derating Curve

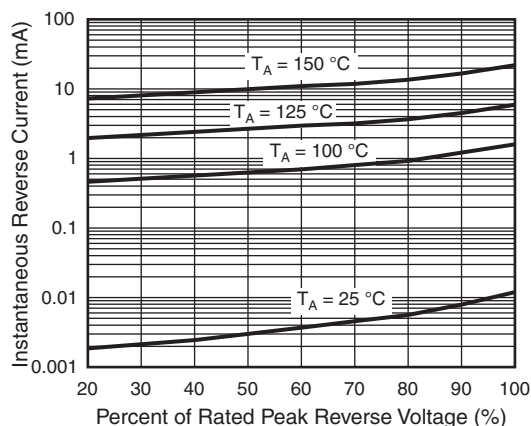


Fig. 4 - Typical Reverse Characteristics Per Diode

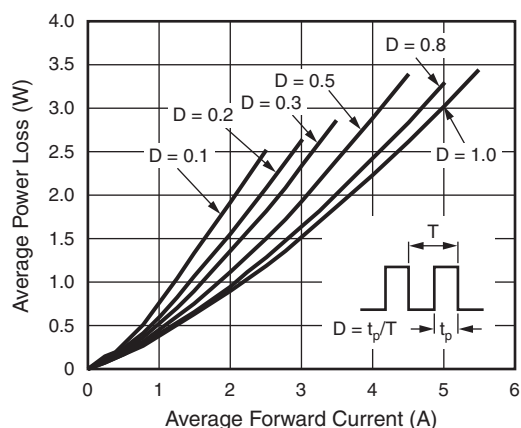


Fig. 2 - Forward Power Loss Characteristics Per Diode

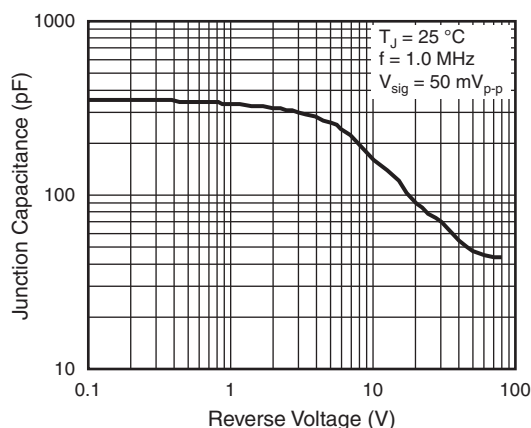


Fig. 5 - Typical Junction Capacitance Per Diode

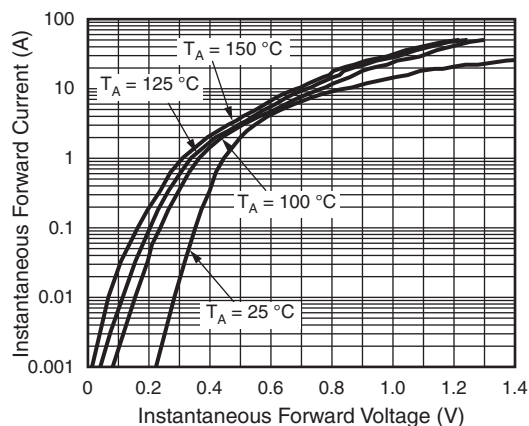


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

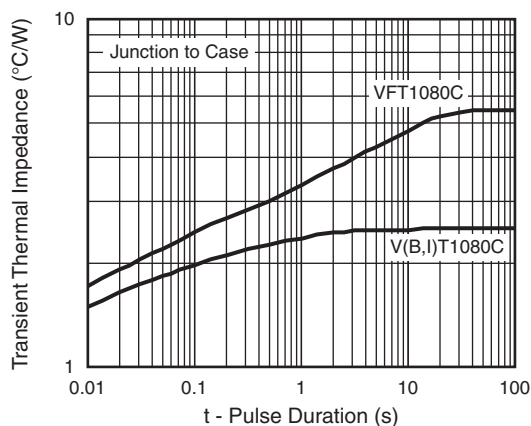
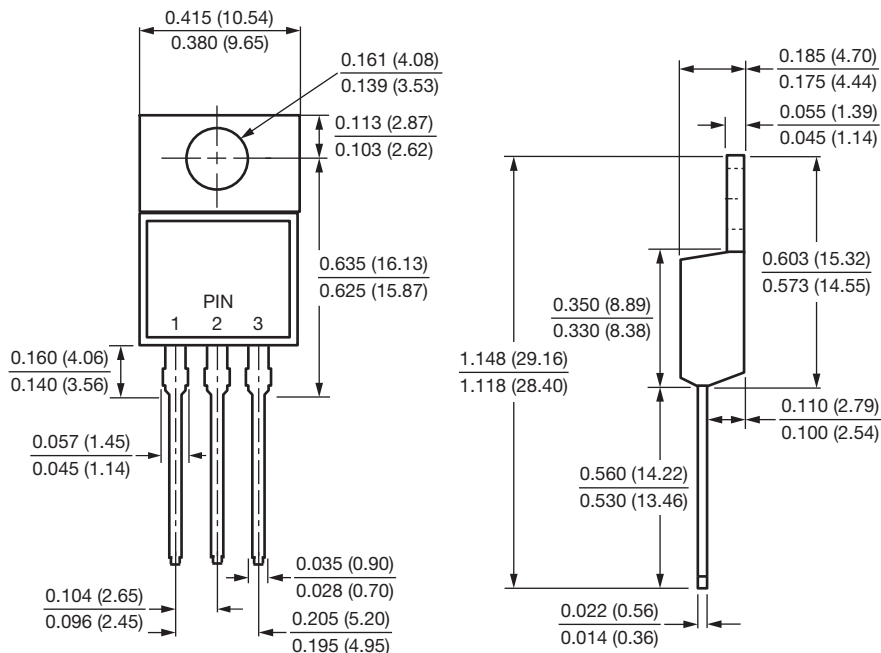


Fig. 6 - Typical Transient Thermal Impedance Per Diode

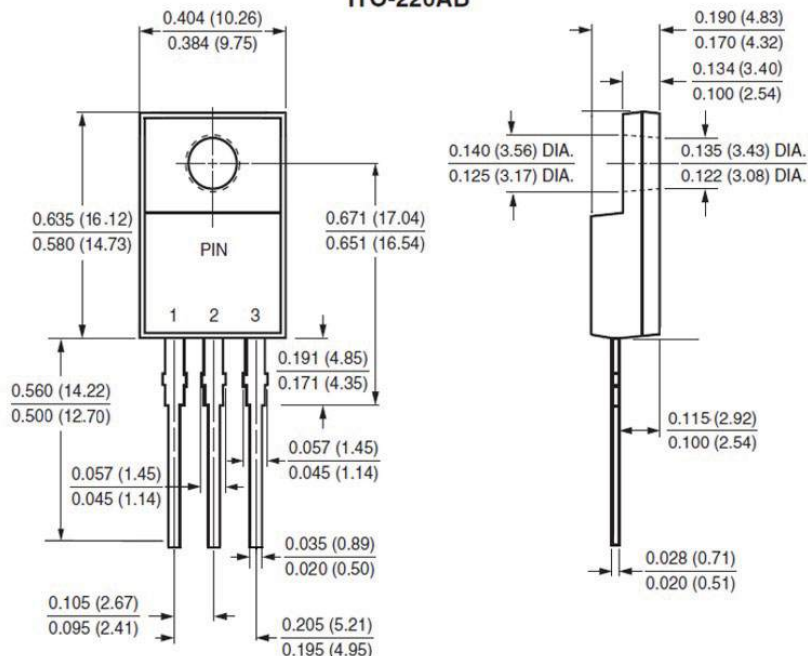


## PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

### TO-220AB



### ITO-220AB

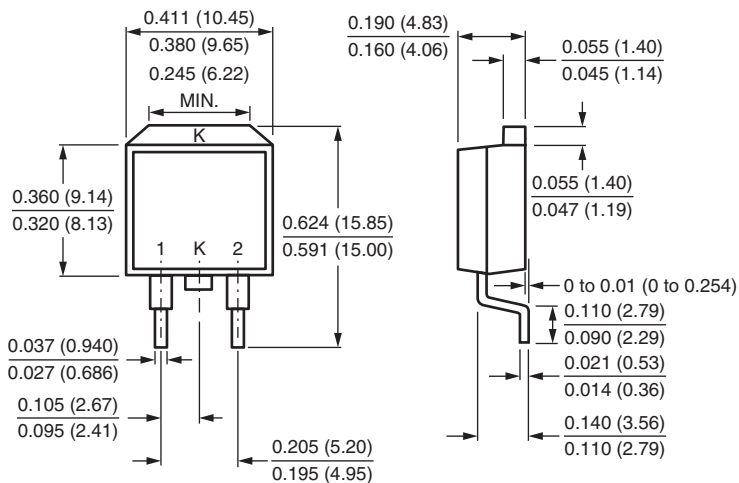




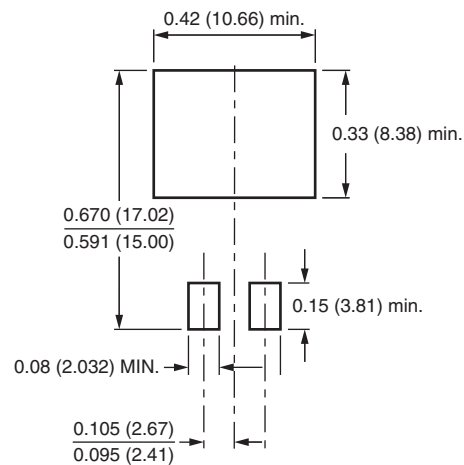
## TO-262AA



## D<sup>2</sup>PAK (TO-263AB)



## Mounting Pad Layout





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